Gesreh History. 10/20/04. J. (5 pp.)

			A.	// /
L Number	Hits		DB	Time stamp
1	2890		USPAT;	2004/10/19 08:37
_		(257/410) or (257/411) or (438/230)).CCLS.	US-PGPUB	
2	3	(((257/288) or (257/408) or (257/409) or	USPAT;	2004/10/19 08:38
		(257/410) or (257/411) or	US-PGPUB;	
		(438/230)).CCLS.) and "without" near3 (ammonia "NH.sub.3")	EPO; JPO; DERWENT;	
		(anunonia Nn. Sub. 3)	IBM TDB	
	244	(nitridization nitride nitriding	USPAT;	2004/10/18 07:41
		nitridizing) near4 (ald atomic adj layer	US-PGPUB;	1 2001, 20, 20
		adj deposition)	EPO; JPO;	
j	,		DERWENT;	
	ĺ		IBM_TDB	
-	18	(nitridization nitride nitriding	USPAT;	2004/10/17 15:01
		nitridizing) near6 (ald atomic adj layer adj deposition) near6 (ammonia "NH.sub.3")	US-PGPUB; EPO; JPO;	
		adj deposition, nearo (anunonia NH.Sub.3)	DERWENT;	
			IBM TDB	}
_	1	(nitridization nitride nitriding	USPAT;	2004/10/17 15:02
		nitridizing) near6 (ald atomic adj layer	US-PGPUB;	
		adj_deposition) and ("without" near3	EPO; JPO;	
		(ammonia "NH.sub.3"))	DERWENT;	
	170	/	IBM_TDB	0004/10/15 15 15
_	179		USPAT;	2004/10/17 15:03
		nitridizing) and silicon adj nitride and ("without" near3 (ammonia "NH.sub.3"))	US-PGPUB; EPO; JPO;	
		("Tellode lieato (ammolita Nii.5db.5))	DERWENT;	
	,		IBM TDB	
_	96	(nitridization nitride nitriding	USPĀT;	2004/10/17 15:03
		nitridizing) and silicon adj nitride and	US-PGPUB;	
		(spacer barrier) and ("without" near3	EPO; JPO;	
		(ammonia "NH.sub.3"))	DERWENT;	
l _	,	(nitridization nitride nitriding	IBM_TDB USPAT;	2004/10/17 15:05
-	-	nitridization mitride mitriding nitride and	US-PGPUB;	2004/10/17 15:05
		(spacer barrier) and ("without" near3	EPO; JPO;	
		(ammonia "NH.sub.3")) and (ald atomic adj	DERWENT;	
	:	layer adj deposition)	IBM TDB	
-	4	(nitridization nitride nitriding	USPĀT;	2004/10/17 15:06
		nitridizing) and ("Si.sub.3 N.sub.4"	US-PGPUB;	
.		<pre>silicon adj nitride) and (spacer barrier) and ("without" near3 (ammonia "NH.sub.3"))</pre>	EPO; JPO;	i i
		and ("without" hears (ammonia "NH.Sub.3")) and (ald atomic adj layer adj deposition)	DERWENT; IBM TDB	
_	4	(nitridization nitride nitriding	USPAT;	2004/10/17 15:06
	_	nitridizing) and ("Si.sub.3N.sub.4"	US-PGPUB;	-551, 25, 17, 15.00
		silicon adj nitride) and (spacer barrier)	EPO; JPO;	
		and ("without" near3 (ammonia "NH.sub.3"))	DERWENT;	
		and (ald atomic adj layer adj deposition)	IBM_TDB	0004/00/55 55
-	4	(nitridization nitride nitriding nitridizing) and ("Si.sub.3"\$1"N.sub.4"	USPAT; US-PGPUB;	2004/10/17 15:06
		silicon adj nitride) and (spacer barrier)	EPO; JPO;	
		and ("without" near3 (ammonia "NH.sub.3"))	DERWENT;	
		and (ald atomic adj layer adj deposition)	IBM TDB	
-	4	("Si.sub.3"\$1"N.sub.4" silicon adj	USPĀT;	2004/10/17 15:06
		nitride) and (spacer barrier) and	US-PGPUB;	
		("without" near3 (ammonia "NH.sub.3")) and	EPO; JPO;	
		(ald atomic adj layer adj deposition)	DERWENT;	
_	5	("Si.sub.3"\$1"N.sub.4" silicon adj	IBM_TDB USPAT;	2004/10/17 15:07
	3	nitride) and ("without" near3 (ammonia	US-PGPUB;	2004/10/17 13:07
		"NH.sub.3")) and (ald atomic adj layer adj	EPO; JPO;	
	ľ	deposition)	DERWENT;	
	_		IBM_TDB	
-	171	(ald atomic adj layer adj	USPAT;	2004/10/17 15:08
		deposition).ti,ab,clm. and silicon adj	US-PGPUB;	
	ļ	nitride.ti,ab,clm.	EPO; JPO;	,
	ł		DERWENT; IBM TDB	
			מחז זחם	

-	2	(ald atomic adj layer adj	USPAT;	2004/10/17 15:10
	Ì	deposition).ti,ab,clm. and silicon adj nitride.ti,ab,clm. and ("without" near4	US-PGPUB;	
		(ammonia "NH.sub.3"))	EPO; JPO; DERWENT;	
		(anunonia wii.sub.s))	IBM TDB	
-	31	pdf adj solutions.as.	USPĀT;	2004/10/17 15:10
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	0	ndf odi colutions on and mituida alm	IBM_TDB USPAT;	2004/10/17 15:21
_	"	pdf adj solutions.as. and nitride.clm.	US-PGPUB;	2004/10/17 15:21
			EPO; JPO;	
			DERWENT;	
	f		IBM TDB	
-	2691		USPAT;	2004/10/19 08:37
		(257/410) or (257/411)).CCLS.	US-PGPUB	
-	. 3	(((257/288) or (257/408) or (257/409) or	USPAT;	2004/10/19 08:38
		(257/410) or (257/411)).CCLS.) and "without" near3 (ammonia "NH.sub.3")	US-PGPUB; EPO; JPO;	
		without hears (anunonia Nr. Sub. 5)	DERWENT;	
	•		IBM TDB	
-	1	(((257/288) or (257/408) or (257/409) or	USPAT;	2004/10/17 15:26
		(257/410) or (257/411)).CCLS.) and	US-PGPUB;	
		"without" near3 (ammonia "NH.sub.3") and	EPO; JPO;	
1		(lightly adj doped adj drain lightly-doped	DERWENT;	
	5	adj drain ldd)	IBM_TDB	2004/10/17 15 25
-) 3	(((257/288) or (257/408) or (257/409) or (257/410) or (257/411)).CCLS.) and (ald	USPAT; US-PGPUB;	2004/10/17 15:36
		atomic adj layer adj deposition) and (ldd	EPO; JPO;	
		lightly adj doped adj drain) and (silicon	DERWENT;	
!		adj nitride "Si.sub.3"\$1"N.sub.4" SiN)	IBM TDB	
-	0		USPAT;	2004/10/17 15:37
		(257/410) or (257/411)).CCLS.) and	US-PGPUB;	
]		(nitride near4 ("without" near4 (ammonia	EPO; JPO;	
		"NH.sub.3"))) and (ldd lightly adj doped	DERWENT;	
		adj drain) and (silicon adj nitride "Si.sub.3"\$1"N.sub.4" SiN)	IBM_TDB	
_	1		USPAT;	2004/10/17 15:42
		(257/410) or (257/411)).CCLS.) and	US-PGPUB;	2001, 10, 17 20112
		("without" near4 (ammonia "NH.sub.3")) and	EPO; JPO;	
		(ldd lightly adj doped adj drain) and	DERWENT;	
	1	(silicon adj nitride "Si.sub.3"\$1"N.sub.4"	IBM_TDB	
_	0	SiN) (((257/288) or (257/408) or (257/409) or	HCDAM.	2004/10/17 15:40
-		((257/288) of (257/408) of (257/409) of (257/410) or (257/411)).CCLS.) and	USPAT;	2004/10/17 15:49
		("without" near4 (ammonia "NH.sub.3")) and	US-PGPUB; EPO; JPO;	
		(ldd lightly adj doped adj drain) and	DERWENT;	
		(silicon adj nitride "Si.sub.3"\$1"N.sub.4"	IBM_TDB	
	_	SiN) and spacer		
-	0	(NO-nitridi?ation	USPAT;	2004/10/17 15:52
		"N.sub.2"\$10-nitridi?ation) and silicon adj nitride and (roxnox ono	US-PGPUB;	
		oxide-nitride-oxide "oxide/nitride/oxide")	EPO; JPO; DERWENT;	
		and (lightly adj doped adj drain ldd)	IBM TDB	
-	0	(NO-nitridi?ation	USPAT;	2004/10/17 15:52
		"N.sub.2"\$10-nitridi?ation) and silicon	US-PGPUB;	
		adj nitride	EPO; JPO;	
		•	DERWENT;	
_	4	((NO "N.sub.2"\$10) near3 nitridi?ation)	IBM_TDB	2004/10/17 16:00
	4	and silicon adj nitride	USPAT; US-PGPUB;	2004/10/17 16:00
		and british day interrus	EPO; JPO;	
l i			DERWENT;	
			IBM_TDB	
-	.0	(atomic adj layer adj deposition ald pecvd	USPAT;	2004/10/17 16:03
		plasma adj enhanced adj chemical adj	US-PGPUB;	
.		vapo\$r adj deposition) near5 "N.sub.2"	EPO; JPO;	
	ļ	<pre>near5 ("SiCl.sub.4" "SiF.sub.4") and (ono roxnox oxide-nitride-oxide)</pre>	DERWENT; IBM TDB	
L		TOWNON ONTRE HITCHINE-ONTRE)	מת ד הום ד	L.,

_	12		USPAT;	2004/10/17 16:08
		plasma adj enhanced adj chemical adj	US-PGPUB;	
		vapo\$r adj deposition) near5 "N.sub.2"	EPO; JPO;	ĺ
		near5 ("SiCl.sub.4" "SiF.sub.4")	DERWENT;	
			IBM_TDB	
-	282	method near6 ono.clm.	USPAT;	2004/10/17 16:09
1			US-PGPUB;	
			EPO; JPO;	
	1		DERWENT;	
			IBM_TDB	
-	0		USPAT;	2004/10/17 16:10
		nitride and (nitridization nitridisation)	US-PGPUB;	•
		near4 (ald atomic adj layer adj deposition	EPO; JPO;	
		pecvd)	DERWENT;	
]			IBM_TDB	
-	207	1	USPAT;	2004/10/17 16:10
		nitride	US-PGPUB;	
			EPO; JPO;	
		·	DERWENT;	
			IBM_TDB	
-	22		USPAT;	2004/10/17 16:13
		nitride and (lightly adj doped adj drain	US-PGPUB;	
		ldd)	EPO; JPO;	
			DERWENT;	
	_		IBM_TDB	0004/05/55 55 5
_	1	,	USPAT;	2004/10/17 16:21
		nitride and ("SiF.sub.4" "SiCl.sub.4") and	US-PGPUB;	
		(lightly adj doped adj drain ldd)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	13	1 2 3 3 3 3 3 3 3 3 3 3 3 3 3 3 3 3 3 3	USPAT;	2004/10/17 16:52
		oxide-nitride-oxide) and silicon adj	US-PGPUB;	
		nitride	EPO; JPO;	
	1		DERWENT;	
			IBM_TDB	
-	1	N-containing adj gas and silicon adj	USPAT;	2004/10/17 16:56
		nitride and spacer and (ldd lightly adj	US-PGPUB;	
		doped adj drain)	EPO; JPO;	
		,	DERWENT;	
	,	At any factor to the control of the	IBM_TDB	0004/10/15 16 56
-	1	N-containing adj gas and silicon adj	USPAT;	2004/10/17 16:56
		nitride and spacer	US-PGPUB;	
			EPO; JPO;	İ
			DERWENT;	
		No anakaining and ana and attitude at	IBM_TDB	0004/10/17 16 57
_	8		USPAT;	2004/10/17 16:57
		nitride	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	311	method near3 (ono oxide-nitride-oxide	IBM_TDB	2004/10/17 16 50
	311	,	USPAT;	2004/10/17 16:58
		roxnox)	US-PGPUB;	
			EPO; JPO;	
•			DERWENT;	
_	122	mothed many? (one and de misselle e lite	IBM_TDB	0004/10/17 17 17
_	137		USPAT;	2004/10/17 17:18
		roxnox).ti,ab,clm.	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	85	(oxide-nitride-oxide ono roxnox) and (ldd	IBM_TDB	2004/10/17 17 07
_	63	lightly adj doped adj drain) and spacer	USPAT;	2004/10/17 17:27
•			US-PGPUB;	
		and etch adj stop	EPO; JPO;	
			DERWENT;	
_	8	etch add stop add layor poor? cilicon add	IBM_TDB	2004/10/17 17:56
-	8		USPAT;	2004/10/17 17:56
		nitride and silicon adj nitride near4	US-PGPUB;	İ
		barrier and (ldd lightly adj doped adj drain)	EPO; JPO;	
	İ	urain)	DERWENT;	
			IBM TDB	

- '	112	(ldd lightly adj doped adj	USPAT;	2004/10/17 18:00
		drain).ti,ab,clm. and silicon adj nitride	US-PGPUB;	
		and ono and 438/\$9.ccls.	EPO; JPO;	
			DERWENT; IBM TDB	
_	0	(ldd lightly adj doped adj	USPAT;	2004/10/17 18:01
		drain).ti,ab,clm. and silicon adj nitride	US-PGPUB;	2004/10/17 10:01
		and ono and 438/\$9.ccls. and (ald atomic	EPO; JPO;	
		adj layer adj deposition)	DERWENT;	
			IBM_TDB	
-	17	' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' '	USPAT;	2004/10/17 18:01
		drain).ti,ab,clm. and silicon adj nitride	US-PGPUB;	
		and ono and 438/\$9.ccls. and (ald atomic	EPO; JPO;	
		adj layer adj deposition pecvd)	DERWENT;	
1_	17	 (ldd lightly adj doped adj	IBM_TDB USPAT;	2004/10/17 18:02
	'	drain).ti,ab,clm. and silicon adj nitride	US-PGPUB;	2004/10/17 18:02
		and ono and 438/\$9.ccls. and (ald atomic	EPO; JPO;	
		adj layer adj deposition pecvd plasma adj	DERWENT;	
		enhanced adj chamical adj vapor adj	IBM TDB	
		deposition)		
-	1		USPAT;	2004/10/18 07:46
		roxnox oxide-nitride-oxide) and spacer and	US-PGPUB;	
		(ldd lightly adj doped adj drain)	EPO; JPO;	,
			DERWENT;	
_	4	double neart silveen add mittaids and town	IBM_TDB	2004/10/10 07:47
_	4	double near4 silicon adj nitride and (ono roxnox oxide-nitride-oxide) and spacer	USPAT; US-PGPUB;	2004/10/18 07:47
		Lownow Owing-Hitting-Owing) and spacer	EPO; JPO;	
			DERWENT;	
	1		IBM TDB	
_	84	method near4 silicon adj nitride near4	USPAT;	2004/10/18 07:51
		spacer and (1dd lightly adj doped adj	US-PGPUB;	
		drain)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	3	method near4 silicon adj nitride near4	USPAT;	2004/10/18 08:25
		spacer and (ldd lightly adj doped adj drain) and (ald atomic adj layer adj	US-PGPUB;	
		deposition)	EPO; JPO; DERWENT;	
			IBM TDB	
-	3	(method near4 silicon adj nitride near4	USPĀT;	2004/10/18 08:28
		spacer and (ldd lightly adj doped adj	US-PGPUB;	
		drain) and (ald atomic adj layer adj	EPO; JPO;	
]	deposition)) and (nitride adj oxide NO	DERWENT;	
-		"N. sub. 20")	IBM_TDB	0001/10/15
-	0	(method near4 silicon adj nitride near4 spacer and (1dd lightly adj doped adj	USPAT;	2004/10/18 08:29
		drain) and (ald atomic adj layer adj	US-PGPUB; EPO; JPO;	
		deposition)) and (nitride adj oxide	DERWENT;	
		"N.sub.20")	IBM TDB	
-	0	(method near4 nitridization and (ldd	USPAT;	2004/10/18 08:29
		lightly adj doped adj drain) and (ald	US-PGPUB;	
		atomic adj layer adj deposition)) and	EPO; JPO;	
		(nitride adj oxide "N.sub.20")	DERWENT;	
		Amarka di mana di matanta di mana di matanta di mana di matanta di mana di matanta di mana di matanta di mana di matanta di mana di matanta di mana di matanta di mana di matanta di mana di matanta di mana di matanta di m	IBM_TDB	0004/10/10
-	0	(method near4 nitridization) and (ldd	USPAT;	2004/10/18 08:30
		lightly adj doped adj drain) and (ald atomic adj layer adj deposition) and	US-PGPUB;	
]		(nitride adj oxide "N.sub.20")	EPO; JPO; DERWENT;	
		(miciae aaj onide N.Sub.20)	IBM TDB	
-	0	(method near4 nitridization) and (ald	USPAT;	2004/10/18 08:30
		atomic adj layer adj deposition) and	US-PGPUB;	
		(nitride adj oxide "N.sub.20")	EPO; JPO;	
			DERWENT;	
].	_	A-11-1 A 12-1-4	IBM_TDB	
-	0	(method near4 nitridization) near6	USPAT;	2004/10/18 08:30
		(nitride adj oxide "N.sub.20")	US-PGPUB;	٠,
			EPO; JPO; DERWENT;	,
			IBM TDB	
			בטנו נוטב	<u> </u>

-	0	method near4 nitridization and ("no" adj2 ammonia)	USPAT; US-PGPUB;	2004/10/18 08:31
			EPO; JPO; DERWENT;	
			IBM TDB	
-	47	method near4 nitridization	USPĀT; US-PGPUB;	2004/10/18 08:31
			EPO; JPO; DERWENT; IBM TDB	
	14	(method near4 nitridization).ti,ab,clm.	USPAT; US-PGPUB;	2004/10/18 08:31
			EPO; JPO; DERWENT;	
-	3	(\	IBM_TDB USPAT;	2004/10/18 08:32
		not (ammonia "NH.sub.3")	US-PGPUB; EPO; JPO;	
			DERWENT; IBM TDB	
-	3	((method near4 nitridization).ti,ab,clm.) not (ammonia "NH.sub.3") and method near4	USPAT;	2004/10/18 08:36
	-	nitridization	US-PGPUB; EPO; JPO;	
			DERWENT; IBM TDB	
-	16	(US-6756634-\$ or US-6436848-\$ or US-5674788-\$ or US-6690046-\$ or	USPĀT; US-PGPUB	2004/10/18 09:17
		US-6744098-\$ or US-6649543-\$ or	US-FGFUB	
		US-6323519-\$ or US-6653184-\$ or US-6682979-\$ or US-6686298-\$ or		
		US-5734185-\$).did. or (US-20040146644-\$ or US-20040137742-\$ or US-20030143792-\$ or		
		US-20020137296-\$ or US-20040042307-\$).did.		
_	0	((US-6756634-\$ or US-6436848-\$ or US-5674788-\$ or US-6690046-\$ or	USPAT; US-PGPUB;	2004/10/18 09:36
		US-6744098-\$ or US-6649543-\$ or US-6323519-\$ or US-6653184-\$ or	EPO; JPO; DERWENT;	
		US-6682979-\$ or US-6686298-\$ or	IBM_TDB	
		US-5734185-\$).did. or (US-20040146644-\$ or US-20040137742-\$ or US-20030143792-\$ or		
		US-20020137296-\$ or US-20040042307-\$).did.) and fu.in.		
-	27	ldd and spacer and silicon adj nitride and	USPAT;	2004/10/18 10:16
	,	ono and ild	US-PGPUB; EPO; JPO;	
			DERWENT; IBM TDB	
-	28	<pre>ild near4 protect\$3 and gate and silicon adj nitride and spacer</pre>	USPĀT;	2004/10/18 10:16
		ad, micride and spacer	US-PGPUB; EPO; JPO;	
			DERWENT; IBM TDB	
-	2	("20020146879").PN.	USPAT; US-PGPUB;	2004/10/18 15:19
			EPO; JPO;	
			DERWENT; IBM TDB	